King Fahd University of Petroleum & Minerals Electrical Engineering Department EE203: Electronics I (072)

| Instructor Information | | Dr. Alaa El-Din Hussein | Office 59-0058 | | Phone 4868 | Email: husseina@kfupm.edu.sa | | Office Hours S, M & W 09:00-09:55 am, M 11:00-11:55 am | |
|---|---|--|--|--|------------|---------------------------------|--|---|----------------------------|
| | | Text | Text Grading | | | | | Attendance | |
| Course Information | | Microelectronic Circuits 5 th ed Sedra & Smith | HW+QuizzesProjectTwo ExamsLabFi15%5%30%20% | | | Final Exam 30% | 6 unexcused absences → Warning 9 unexcused absences → DN | | |
| | Week | | Topics to cover | | | | | Sec | Lab Activity |
| 1 | Feb 16 – | 20 Diodes: Introduction, Ideal operation of the diode. | n, Terminal chara | nal characteristics of the diode, Physical | | | 1, 2, 7 | No Lab | |
| 2 | Feb 23 - | b 23 - 27 Graphical and analytical diode circuits analysis, Diode Models, the Zener diode. | | | | | 3 | 3.1-3.3, 3.5, 3.6, 4.1, 4.2 | Exp 1: Lab Equipment |
| 3 | March 1 | Diode applications: half and Full-wave rectifiers, Limiting and Clamping circuits and voltage doublers. Field-Effect Transistors (FETs): Device structure and operation. | | | | | 3 4 | 5.1-5.4, 6 1.1-1.5 | Exp 2: Pspice |
| 4 | March 8 - 12 PMOS structure and operation, CMOS structure, Current –Voltage Characteristic, Role of substrate, MOSFET Circuits at DC. | | | | | | | 1.6-1.8, 2.1-2.5, 3 | Exp 3: Diode Applications |
| Exam 1 Wed March 19 (6:00-8:00 pm) | | | | | | | | | |
| 5 | March 15 | | The MOSFET as amplifier, Biasing, small signal operation and models, Single stage amplifier (CS, CG and CD). | | | | | | No Lab |
| 6 | March 22 | , | Single stage amplifier (Continued) (CS, CG & CD). | | | | | 7 | Exp 4: DC Power Supply |
| 7 | March 29 - / | | Bipolar Junction Transistors (BJTs): structure and operation, types, symbols and conventions, transistors current-voltage characteristics. | | | | | 1.1-1.3, 1.5, 1.6, 2, 3 | Exp 5: MOSFET Amplifiers |
| 8 | April 5 | | BJT circuits at DC, Biasing, Small signal models and analysis. | | | | | | Exp 6: BJT Characteristics |
| Midterm Vacation April 12-16 | | | | | | | | | |
| 9 | April 19 | - 23 Single stage amplifier (CE | Single stage amplifier (CE, and CB). | | | | | 7.1-7.5 7.6,7.7 | No Lab |
| 10 | April 26 | | Single stage amplifier (CC). Differential Amplifiers: MOS. | | | | | | Exp 7: BJT CE Amplifiers |
| 11 | May 3 – | BIT Differential amplifiers | | | | | 7 | 1,2 3 1.1, 1.2, 2.1, 2.2 | No Lab |
| Exam 2 Wed May 14 (6:00-8:00 pm, Building 10) | | | | | | | | | |
| 12 | May 10- | | CMOS Logic circuits, CMOS transistor sizing. | | | | | | Exp 8: Differential Amp. |
| 13 | May 17- | Pass transistor logic circuit | Pass transistor logic circuits (PTL), Basic concept of dynamic logic circuits. BJT as a switch, The | | | | | | Exp 9: CMOS Inverter |
| 14 | May 24- | | RTL circuits, maximum fan-out calculation, ECL logic circuits. | | | | | | Exp 10: BJT Logic Gates |
| 15 | May 31 - Ju | - June 4 TTL Basic Inverters and NAND gate, BJT vs. MOS Logic: advantage/disadvantages. | | | | | | Handout | Lab Final |

Final Exam Monday June 9, 2008 @ 7:00PM